HIGH SPEED 3.3V 2K X 8 DUAL-PORT STATIC RAM WITH INTERRUPTS

LEAD FINISH (SnPb) ARE IN EOL PROCESS - LAST TIME BUY EXPIRES JUNE 15, 2018

Features

- High-speed access
 - Commercial & Industrial: 25/35/55ns (max.)
 - Low-power operation
 - IDT71V321S
 Active: 325mW (typ.)
 Standby: 5mW (typ.)
 IDT71V321L
 - IDT/TV321L
 Active: 325mW (typ.)
 Standby: 1mW (typ.)
- Two INT flags for port-to-port communications

- On-chip port arbitration logic (IDT71V321 only)
- **BUSY** output flag
- Fully asynchronous operation from either port
- Battery backup operation—2V data retention (L only)
- TTL-compatible, single 3.3V power supply
- Available in 52-pin PLCC, 64-pin TQFP and STQFP packages
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information



NOTES:

- 1. IDT71V321 (MASTER): BUSY is an output
- 2. BUSY and INT are totem-pole outputs.

JANUARY 2018

IDT71V321S/L High Speed 3.3V 2K x 8 Dual-Port Static RAM with Interrupts

Industrial and Commercial Temperature Ranges

Description

The IDT71V321 is a high-speed 2K x 8 Dual-Port Static RAMs with internal interrupt logic for interprocessor communications. The IDT71V321 is designed to be used as a stand-alone 8-bit Dual-Port RAM.

The device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by \overline{CE} , permits the on chip circuitry of each

port to enter a very low standby power mode.

Fabricated using CMOS high-performance technology, these devices typically operate on only 325mW of power. Low-power (L) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT71V321 devices are packaged in a 52-pin PLCC, a 64-pin TQFP (thin quad flatpack), and a 64-pin STQFP (super thin quad flatpack).



Pin Configurations^(1,2,3)

5. This text does not indicate orientation of the actual part-marking.

IDT71V321S/L High Speed 3.3V 2K x 8 Dual-Port Static RAM with Interrupts

Industrial and Commercial Temperature Ranges

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit	
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V	
Та	Operating Temperature 0 to +70			
Tbias	Temperature Under Bias	-55 to +125	٥c	
Tstg	Storage Temperature	-65 to +150	٥C	
Ιουτ	DC Output Current	50	mA	

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.

Capacitance⁽¹⁾

 $(TA = +25^{\circ}C, f = 1.0MHz)$ TQFP Only

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF
				3026 tbl 04

NOTES:

1. This parameter is determined by device characterization but is not production tested.

3dv references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

h from 0V to 3V or from 3V to 0V.

			71V:	321S	71V321L		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
L	Input Leakage Current ⁽¹⁾	$V_{CC} = 3.6V,$ $V_{IN} = 0V$ to V_{CC}		10		5	μA
LO	Output Leakage Current	\overline{CE} = VIH, Vout = 0V to Vcc Vcc = 3.6V		10	-	5	μA
Vol	Output Low Voltage	Iol = 4mA		0.4		0.4	V
Vон	Output High Voltage	Юн = -4mA	2.4		2.4	I	V

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 3.3V ± 0.3V)

NOTE:

1. At Vcc < 2.0V input leakages are undefined.

3026 tbl 05

Recommended OperatingTemperature and Supply VoltageGradeAmbientGNDVcc

Grade	Temperature	GND	VCC
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V
NOTEO			3026 tbl 02

NOTES:

3026 tbl 01

1. This is the parameter TA. This is the "instant on" case temperature.

 Industrial temperature: for specific speeds, packages and powers contact your sales office.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	3.0	3.3	3.6	V
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.0		VCC+0.3 ⁽²⁾	V
VIL	Input Low Voltage	-0.3(1)	_	0.8	V
				:	3026 tbl 03

NOTES:

1. VIL (min.) = -1.5V for pulse width less than 20ns.

2. VTERM must not exceed Vcc + 0.3V.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(1,2)}$ (Vcc = 3.3V ± 0.3V)

						21X25 & Ind		21X35 & Ind		21X55 & Ind	
Symbol	Parameter	Test Condition	Versi	on	Тур.	Max.	Тур.	Max.	Тур.	Max.	Un
lcc	Dynamic Operating Current	$\overline{CE} = VIL$, Outputs Disabled SEM = VIH	COM'L	S L	55 55	130 100	55 55	125 95	55 55	115 85	m
	(Both Ports Active)	$f = fMAX^{(3)}$	IND	L	55	130	55	125	55	115	
ISB1	Standby Current (Both Ports - TTL	$\frac{\overline{CE}_{R}}{\overline{SEM}_{R}} = \frac{\overline{CE}_{L}}{\overline{SEM}_{L}} = V_{H}$	COM'L	S L	15 15	35 20	15 15	35 20	15 15	35 20	m
	Level Inputs)	$f = fMAX^{(3)}$	IND	L	15	35	15	35	15	35	
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}^{"A"} = V_{IL}$ and $\overline{CE}^{"B"} = V_{IH}^{(5)}$ Active Port Outputs Disabled,	COM'L	S L	25 25	75 55	25 25	70 50	25 25	60 40	n
	Level inputs)	$\frac{f=f_{MAX}^{(3)}}{\overline{SEM}_{R}} = \overline{\overline{SEM}}_{L} = V_{IH}$	IND	L	25	75	25	70	25	60]
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports CEL and CER ≥ Vcc - 0.2V Vℕ > Vcc - 0.2V or	COM'L	S L	1.0 0.2	5 3	1.0 0.2	5 3	1.0 0.2	5 3	n
		$\frac{V_{IN} \leq}{SEM_{R}} = \frac{0}{SEM_{L}} \geq V_{CC} - 0.2V$	IND	L	0.2	6	1.0	5	1.0	5	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\label{eq:cellson} \begin{array}{l} \overline{CE}^{*}\text{A}^* & \leq 0.2 \text{V} \text{ and} \\ \overline{CE}^{*}\text{B}^* & \geq V \underline{Cc} & - 0.2 \text{V}^{(5)} \\ \overline{SEMR} & = \overline{SEML} \geq V \underline{Cc} & - 0.2 \text{V} \end{array}$	COM'L	S L	25 25	70 55	25 25	65 50	25 25	55 40	n
	Civics Level Inpuls)	SEMIR = SEMIL \geq VCC - 0.2V VIN \geq VCC - 0.2V or VIN \leq 0.2V Active Port Outputs Disabled f = fmax ⁽³⁾	IND	L	25	70	25	65	25	55	

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

2. Vcc = 3.3V, TA = +25°C, and are not production tested. Icccc = 70mA (Typ.).

3. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc and using "AC Test Conditions" of input levels of GND to 3V.

4. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.

5. Port "A" may be either left or right port. Port "B" is opposite from port "A".

Data Retention Characteristics (L Version Only)

Symbol	Parameter	Test Condition		Min.	Тур. ⁽¹⁾	Max.	Unit
Vdr	VCC for Data Retention			2.0	_	0	V
ICCDR	Data Retention Current	Vcc = 2v, CE <u>></u> Vcc - 0.2V	COM'L.	_	100	500	μA
tcdr ⁽³⁾	Chip Deselect to Data	$V \text{IN} \geq V \text{CC}$ - 0.2V or $V \text{IN} \leq 0.2 V$	IND.	_	100	1000	μA
	Retention Time			0	_	_	V
tR ⁽³⁾	Operation Recovery Time			tRC ⁽²⁾	_	_	V

NOTES:

1. Vcc = 2V, TA = +25°C, and is not production tested.

2. tRC = Read Cycle Time.

3. This parameter is guaranteed by device characterization but not production tested.

3026 tbl 07



for tHz, tLz, twz, and tow) * Including scope and jig.

3026 tbl 09

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽²⁾

		71V321X25 Com'l & Ind		-	71V321X35 Com'l & Ind		71V321X55 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	25		35	1	55		ns
taa	Address Access Time		25		35		55	ns
tace	Chip Enable Access Time		25		35	_	55	ns
taoe	Output Enable Access Time		12		20		25	ns
toн	Output Hold from Address Change	3	-	3		3		ns
tlz	Output Low-Z Time ^(1,2)	0		0		0		ns
tHZ	Output High-Z Time ^(1,2)		12		15		30	ns
tpu	Chip Enable to Power Up Time ⁽²⁾	0		0		0		ns
tpd	Chip Disable to Power Down Time ⁽²⁾		50		50		50	ns

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested.

3. 'X' in part numbers indicates power rating (S or L).



NOTES:

- 1. $R/\overline{W} = V_{IH}$, $\overline{CE} = V_{IL}$, and is $\overline{OE} = V_{IL}$. Address is valid prior to the coincidental with \overline{CE} transition LOW.
- 2. tbdd delay is required only in the case where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relationship to valid output data.
- 3. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.



Timing Waveform of Read Cycle No. 2, Either Side⁽³⁾

NOTES:

- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 2. Timing depends on which signal is de-asserted first, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 3. $R/\overline{W} = V_{H}$ and the address is valid prior to or coincidental with \overline{CE} transition LOW.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁴⁾

			71V321X25 Com'l & Ind		71V321X35 Com'l & Ind		71V321X55 Com'l & Ind	
Symbol	Parameter	Min.	Мах.	Min.	Мах.	Min.	Max.	Unit
WRITE C	YCLE	•						
twc	Write Cycle Time	25		35		55		ns
tew	Chip Enable to End-of-Write	20		30		40		ns
taw	Address Valid to End-of-Write	20		30		40		ns
tas	Address Set-up Time	0		0		0		ns
twp	Write Pulse Width	20		30		40		ns
twr	Write Recovery Time	0		0		0		ns
tdw	Data Valid to End-of-Write	12		20		20		ns
tнz	Output High-Z Time ^(1,2)		12		15		30	ns
tdн	Data Hold Time ⁽³⁾	0		0		0		ns
twz	Write Enable to Output in High-Z ^(1,2)		15		15		30	ns
tow	Output Active from End-of-Write ^(1,2)	0		0		0		ns

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization but is not production tested.

3. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

4. 'X' in part numbers indicates power rating (S or L).

Timing Waveform of Write Cycle No. 1, (R/W Controlled Timing)^(1,5,8)



Timing Waveform of Write Cycle No. 2, (CE Controlled Timing)^(1,5)



3026 drw 09

NOTES:

- 1. R/\overline{W} or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of \overline{CE} = VIL and R/W= VIL.
- 3. two is measured from the earlier of \overline{CE} or $\overline{R/W}$ going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the RW LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.
- 7. This parameter is determined to be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If \overline{OE} is LOW during a RW controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \overline{OE} is HIGH during a RW controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

3026 tbl 11

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾

		71V321X25 Com'l & Ind		71V321X35 Com'l & Ind		71V321X55 Com'l & Ind			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	
BUSY Tin	ning								
tbaa	BUSY Access Time from Address	_	20		20	_	30	ns	
tbda	BUSY Disable Time from Address	_	20		20	_	30	ns	
t BAC	BUSY Access Time from Chip Enable	_	20		20		30	ns	
tBDC	BUSY Disable Time from Chip Enable	_	20		20	_	30	ns	
twн	Write Hold After BUSY ⁽⁵⁾	12		15		20		ns	
twdd	Write Pulse to Data Delay ⁽¹⁾		50		60		80	ns	
todd	Write Data Valid to Read Data Delay ⁽¹⁾		35		45		65	ns	
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5		5		ns	
tbdd	BUSY Disable to Valid Data ⁽³⁾		30		30		45	ns	

NOTES:

1. Port-to-port delay through RAM cells from the writing port to the reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY."

2. To ensure that the earlier of the two ports wins.

3. tBDD is a calculated parameter and is the greater of 0, twDD - twp (actual) or tDDD - tDw (actual).

4. To ensure that a write cycle is inhibited on port "B" during contention on port "A".

5. To ensure that a write cycle is completed on port "B" after contention on port "A".

6. 'X' in part numbers indicates power rating (S or L).

Timing Waveform of Write with Port-to-Port Read and **BUSY**^(2,3,4)



NOTES:

1. To ensure that the earlier of the two ports wins.

 $2. \quad \overline{C}\overline{E}\mathsf{L}=\overline{C}\overline{E}\mathsf{R}=V\mathsf{I}\mathsf{L}$

3. $\overline{OE} = V_{IL}$ for the reading port.

4. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of Write with **BUSY**⁽³⁾



NOTES:

1. twi must be met for $\overline{\text{BUSY}}$ output 71V321.

2. BUSY is asserted on port 'B' blocking R/W'B', until BUSY'B' goes HIGH.

3. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of **BUSY** Arbitration Controlled by **CE** Timing⁽¹⁾



Timing Waveform of $\overline{\text{BUSY}}$ Arbitration Controlled by Address Match Timing^{(1)}



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

2. If taps is not satisfied, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted.

Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾

		71V321X25 Com'l & Ind			21X35 & Ind	71V321X55 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Мах.	Unit
INTERRU	PT TIMING		-					
tas	Address Set-up Time	0		0		0	_	ns
twr	Write Recovery Time	0	_	0		0	_	ns
tins	Interrupt Set Time		25		25		45	ns
tinr	Interrupt Reset Time		25		25		45	ns
	•						•	3026 tbl 12

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

Timing Waveform of Interrupt Mode⁽¹⁾



CLEAR INT ADDR"B" $\overline{OE"B"}$ $\overline{INT"B"}$ $\overline{INT"B"}$ 3026 drw 15

NOTES:

1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

2. See Interrupt Truth Table.

- 3. Timing depends on which enable signal ($\overline{\text{CE}}$ or R/W) is asserted last.
- 4. Timing depends on which enable signal ($\overline{\text{CE}}$ or R/W) is de-asserted first.

Truth Tables

Table I - Non-Contention Read/Write Control⁽⁴⁾

	Left or	Right R	Port ⁽¹⁾	
R/W	ĒĒ	ŌĒ	D0-7	Function
х	Н	Х	Z	Port Deselected and in Power- Down Mode. Isb2 or Isb4
х	Η	Х	Z	$\overline{CER} = \overline{CEL} = VIH$, Power-Down Mode Isb1 or Isb3
L	L	Х	DATAIN	Data on Port Written Into Memory ⁽²⁾
Н	L	L	DATAOUT	Data in Memory Output on Port ⁽³⁾
Н	L	Η	Z	High-impedance Outputs

NOTES:

3026 tbl 13

1. AOL - A1OL \neq AOR - A1OR.

2. If $\overline{\text{BUSY}} = L$, data is not written.

3. If $\overline{\text{BUSY}}$ = L, data may not be valid, see twod and tood timing. 4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = High-impedance.

Table II — Interrupt Flag^(1,4)

Left Port				Right Port						
R/₩L	ĊĒ∟	OEL	A10L-A0L	ĪNT∟	R/WR	ĊĒr	OE R	A10R-A0R	ĪNTR	Function
L	L	Х	7FF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	7FF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	7FE	Х	Set Left INTL Flag
Х	L	L	7FE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag

NOTES:

1. Assumes $\overline{BUSY}_{L} = \overline{BUSY}_{R} = V_{H}$

2. If $\overline{\text{BUSY}}_{L} = V_{IL}$, then No Change.

3. If $\overline{\text{BUSY}}_{R} = V_{IL}$, then No Change.

4. 'H' = HIGH, 'L' = LOW, 'X' = DON'T CARE

Table III - Address BUSY Arbitration

	In	puts	Out	puts	
ĒĒ∟	CE R	AOL-A10L Aor-A10r	BUSYL ⁽¹⁾	BUSY _R ⁽¹⁾	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

- 1. Pins BUSYL and BUSYR are both outputs. BUSYx outputs on the IDT71V321 are totempole.
- 2. L'if the inputs to the opposite port were stable prior to the address and enable inputs of this port. 'H' if the inputs to the opposite port became stable after the address and enable inputs of this port. If the sis not met, either \overline{BUSY} L or \overline{BUSY} R = LOW will result. \overline{BUSY} L and \overline{BUSY} R outputs can not be LOW simultaneously.
- 3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

3026 tbl 14

3026 tbl 15

IDT71V321S/L High Speed 3.3V 2K x 8 Dual-Port Static RAM with Interrupts

Industrial and Commercial Temperature Ranges

Functional Description

The IDT7V1321 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT71V321 has an automatic power down feature controlled by \overline{CE} . The \overline{CE} controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{CE} = V_{||}$). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INTL}) is asserted when the right port writes to memory location 7FE (HEX), where a write is defined as the $\overline{CER} = R/\overline{WR} = V_{IL}$ per Truth Table II. The left port clears the interrupt by accessing address location 7FE when $\overline{CEL} = \overline{OEL} = V_{IL}$, R/W is a "don't care". Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 7FF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must access the memory location 7FF. The message (8 bits) at 7FE or 7FF is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, address locations 7FE and 7FF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table II for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a busy indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY Logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation.

Depth Expansion

The **BUSY** arbitration, is based on the chip enable and address signals only. It ignores whether an access is a read or write.

The BUSY outputs on the IDT71V321 are totem-pole type outputs and do not require pull-up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate



Figure 3. Busy and chip enable routing for depth expansion with IDT71V321.



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NOTES:

1. Contact your sales office Industrial temperature range is available for selected speeds, packages and powers.

2. Green parts available. For specific speeds, packages and powers contact your local sales office.

LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice - PDN# SP-17-02

Datasheet Document History

03/24/99:		Initiated datasheet document history
		Converted to new format
		Cosmetic and typographical corrections
0 (11 5 10 0	Page 2	Added additional notes to pin configurations
06/15/99:		Changed drawing format
10/15/99:	Page 12	Changed open drain to totem-pole in Table III, note 1
10/21/99:	Page 13	Deleted 'does not' in copy from Busy Logic
11/12/99:		Replaced IDT logo
01/12/01:	Pages 1 & 2	Moved full "Description" to page 2 and adjusted page layouts
	Page 3	Increased storage temperature parameters
	Ū	Clarified TA parameter
	Page 4	DC Electrical parameters-changed wording from "open" to "disabled"
	Ũ	Changed ±200mV to 0mV in notes
08/22/01:	Pages 4, 5, 7,	Industrial temp range offering removed from DC & AC Electrical Characteristics for 35 and 55ns
	9 & 11	
01/17/06:	Page 1	Added green availability to features
	Page 14	Added green indicator to ordering information
	Page 1 & 14	Replaced old IDTTM with new IDTTM logo
	č	Datasheet document history continued on page 15

Datasheet Document History (con't)

08/25/06:	Page 11 Changed INT "A" to INT "B" in the CLEAR INT drawing in the Timing Waveform of Interrupt Mode
10/23/08:	Page 14 Removed "IDT" from orderable part number
01/25/10:	Page 4 In order to correct the DC Chars table for the 71V321/71V421L35 speed grade and the Data Retention Chars
	table, I Temp values have been added to each table respectively. In addition, all of the AC Chars tables and the
	ordering information also now reflect this I temp correction
06/25/15:	Page 2 Removed IDT in reference to fabrication
	Page 2 & 14 The package codes J52-1, PN64-1 & PP64-1 changed to J52, PN64 & PP64 respectively to match standard package codes
	Page 14 Added Tape and Reel indicator to Ordering Information
10/14/15:	Page 1-15 Removed 71V421S/L from the part number, in the pin configurations and throughout the datasheet
	Page 1 - 15 Removed all references to Master/Slave throughout the datasheet
	Page 1-15 Updated the Com'l and Ind speeds for the 25/35/55ns offerings in Features, in the DC & AC Chars tables, in the
	Ordering Information and throughout the datasheet
	Page 13 Removed Width Expansion with Busy Logic Master/Slave Arrays diagram for part numbers 71V321/71V421S/L
	and updated with a Depth Expansion diagram for the single part number 71V321S/L
	Updated the corresponding Depth Expansion descriptive text in the Depth Expansion section of the datasheet
01/12/18:	Product Discontinuation Notice - PDN# SP-17-02
01/12/18:	Product Discontinuation Notice - PDN# SP-17-02 Last time buy expires June 15, 2018



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71V321L25PF71V321L25TF71V321L25JI71V321L25JG71V321L25JG871V321L25JI871V321L25PF871V321L25TF871V321L25PFGI71V321S35TF71V321S55TF871V321S35PF71V321L25TFGI71V321S55J871V321S35J71V321S35TF871V321S35PF871V321S25J71V321S55PF871V321S25J71V321S25J871V321L55J871V321L35TF871V321L35JG871V321L35PF871V321S25J871V321L25TF871V321L25J871V321L55PF871V321S25TF871V321S25PF871V321L25PFG71V321L25PFG71V321L25TF171V321L25TFG71V321L55PF871V321S25FF871V321L25J71V321L25PFG71V321L25PFG71V321L25TF171V321L25TFG71V321L25TF1871V321L35JG71V321L25J71V321L35PF71V321L35J71V321L35J871V321L25TF1871V321L35JG71V321L35PF71V321L35PF71V321L35J871V321L25TF1871V321L35JG71V321L35PF71V321L35PF71V321L35J871V321L25TF1871V321L35JF71V321L35PFGI71V321L35J871V321L35J871V321L25TF1871V321L35JF71V321L35PFGI71V321L35J871V321L35J871V321L25TF1871V321L35PF71V321L35PFGI71V321L35J871V321L35J871V321L25TF1871V321L35PF71V321L35PFGI71V321L35J871V321L35J871V321L25TF1871V321L35PF71V321L35PFGI71V321L35PFGI71V321L35J871V321L25TF1871V321L35PFGI71V321L35PFGI71V321L35PFGI71V321L35J871V321L35JGI71V321L35PFGI71V321L35PFGI71V321L35DF